

Document Title

256K x16 bit Super Low Power and Low Voltage Full CMOS Static RAM

Revision History

| <u>Revision No.</u> | <u>History</u>                                                                                                                                                                                                                                                                                                                                                                                                                          | <u>Draft Date</u> | <u>Remark</u> |
|---------------------|-----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-------------------|---------------|
| 0.0                 | Initial Draft                                                                                                                                                                                                                                                                                                                                                                                                                           | April 2, 1998     | Advance       |
| 0.1                 | Revise<br>- Speed bin change : 70/100ns → 85/100ns<br>- DC characteristics change<br>I <sub>OL</sub> : 0.5mA → 0.1mA<br>I <sub>OH</sub> : -0.5mA → -0.1mA<br>I <sub>SB1</sub> : Super low power product=1μA → 2μA<br>I <sub>DR</sub> : 3/1μA(LL/SL, V <sub>CC</sub> =1.5V) → 3/2μA(LL/SL, V <sub>CC</sub> =1.2V)<br>- 48-CSP package dimension change<br>Die thickness : 0.32mm → 0.45mm<br>E : 0.80mm → 0.93mm<br>E1 : 0.55mm → 0.68mm | June 27, 1998     | Advance       |
| 0.11                | Errata correction                                                                                                                                                                                                                                                                                                                                                                                                                       | August 17, 1998   |               |

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## 256K x 16 bit Low Power and Low Voltage Full CMOS Static RAM

### FEATURES

- Process Technology : Full CMOS
- Organization : 256K x16 bit
- Power Supply Voltage : 1.7 ~ 2.2V
- Low Data Retention Voltage : 1.0V(Min)
- Three state output status and TTL Compatible
- Package Type : 48 - CSP with 0.75mm ball pitch

### GENERAL DESCRIPTION

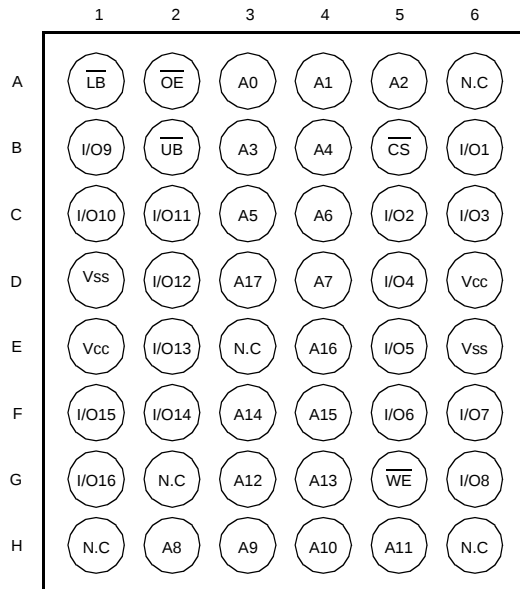
The K6F4016R4M families are fabricated by SAMSUNG's advanced full CMOS process technology. The family supports industrial temperature range and 48 ball Chip Scale Package for user flexibility of system design. The family also supports low data retention voltage for battery back-up operation with low data retention current.

### PRODUCT FAMILY

| Product Family | Operating Temperature  | Vcc Range  | Speed(ns)             | Power Dissipation    |                       | PKG Type |
|----------------|------------------------|------------|-----------------------|----------------------|-----------------------|----------|
|                |                        |            |                       | Standby (Isb1, Typ.) | Operating (Icc1, Max) |          |
| K6F4016R4M-I   | Industrial(-40 ~ 85°C) | 1.7 ~ 2.2V | 85 <sup>1)</sup> /100 | 0.5μA                | 3mA                   | 48-CSP   |

1. The parameter is measured with 30pF test load.

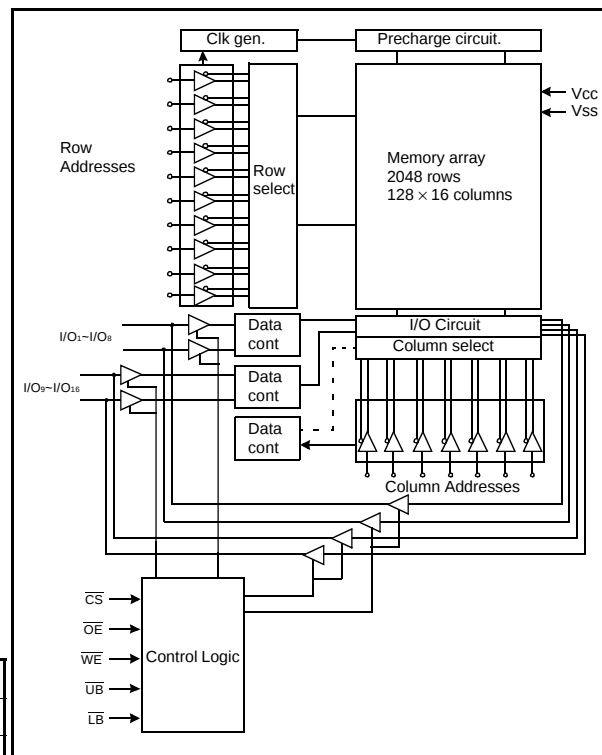
### PIN DESCRIPTION



48-ball CSP - Top View (Ball Down)

| Name            | Function            | Name            | Function            |
|-----------------|---------------------|-----------------|---------------------|
| $\overline{CS}$ | Chip Select Input   | Vcc             | Power               |
| $\overline{OE}$ | Output Enable Input | Vss             | Ground              |
| $\overline{WE}$ | Write Enable Input  | $\overline{UB}$ | Upper Byte(I/O9~16) |
| A0~A17          | Address Inputs      | $\overline{LB}$ | Lower Byte(I/O1~8)  |
| I/O1~I/O16      | Data Inputs/Outputs | N.C.            | No Connection       |

### FUNCTIONAL BLOCK DIAGRAM



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## PRODUCT LIST

| Industrial Temperature Product (-40~85°C) |                                      |
|-------------------------------------------|--------------------------------------|
| Part Name                                 | Function                             |
| K6F4016R4M-ZI85                           | 48-CSP with 48 ball, 85ns, 1.8/2.0V  |
| K6F4016R4M-ZI10                           | 48-CSP with 48 ball, 100ns, 1.8/2.0V |

## FUNCTIONAL DESCRIPTION

| $\overline{\text{CS}}$ | $\overline{\text{OE}}$ | $\overline{\text{WE}}$ | $\overline{\text{LB}}$ | $\overline{\text{UB}}$ | I/O <sub>1-8</sub> | I/O <sub>9-16</sub> | Mode             | Power   |
|------------------------|------------------------|------------------------|------------------------|------------------------|--------------------|---------------------|------------------|---------|
| H                      | X <sup>1)</sup>        | X <sup>1)</sup>        | X <sup>1)</sup>        | X <sup>1)</sup>        | High-Z             | High-Z              | Deselected       | Standby |
| X <sup>1)</sup>        | X <sup>1)</sup>        | X <sup>1)</sup>        | H                      | H                      | High-Z             | High-Z              | Deselected       | Standby |
| L                      | H                      | H                      | L                      | X <sup>1)</sup>        | High-Z             | High-Z              | Output Disabled  | Active  |
| L                      | H                      | H                      | X <sup>1)</sup>        | L                      | High-Z             | High-Z              | Output Disabled  | Active  |
| L                      | L                      | H                      | L                      | H                      | Dout               | High-Z              | Lower Byte Read  | Active  |
| L                      | L                      | H                      | H                      | L                      | High-Z             | Dout                | Upper Byte Read  | Active  |
| L                      | L                      | H                      | L                      | L                      | Dout               | Dout                | Word Read        | Active  |
| L                      | X <sup>1)</sup>        | L                      | L                      | H                      | Din                | High-Z              | Lower Byte Write | Active  |
| L                      | X <sup>1)</sup>        | L                      | H                      | L                      | High-Z             | Din                 | Upper Byte Write | Active  |
| L                      | X <sup>1)</sup>        | L                      | L                      | L                      | Din                | Din                 | Word Write       | Active  |

1. X means don't care. (Must be low or high state)

## ABSOLUTE MAXIMUM RATINGS<sup>1)</sup>

| Item                                                          | Symbol                             | Ratings      | Unit |
|---------------------------------------------------------------|------------------------------------|--------------|------|
| Voltage on any pin relative to V <sub>SS</sub>                | V <sub>IN</sub> , V <sub>OUT</sub> | -0.2 to 3.0V | V    |
| Voltage on V <sub>CC</sub> supply relative to V <sub>SS</sub> | V <sub>CC</sub>                    | -0.2 to 3.6V | V    |
| Power Dissipation                                             | P <sub>D</sub>                     | 1.0          | W    |
| Storage temperature                                           | T <sub>STG</sub>                   | -55 to 150   | °C   |
| Operating Temperature                                         | T <sub>A</sub>                     | -40 to 85    | °C   |

1. Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. Functional operation should be restricted to recommended operating condition. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

RECOMMENDED DC OPERATING CONDITIONS<sup>1)</sup>

| Item               | Symbol          | Min                | Typ     | Max                                | Unit |
|--------------------|-----------------|--------------------|---------|------------------------------------|------|
| Supply voltage     | V <sub>CC</sub> | 1.7                | 1.8/2.0 | 2.2                                | V    |
| Ground             | V <sub>SS</sub> | 0                  | 0       | 0                                  | V    |
| Input high voltage | V <sub>IH</sub> | 1.4                | -       | V <sub>CC</sub> +0.2 <sup>2)</sup> | V    |
| Input low voltage  | V <sub>IL</sub> | -0.2 <sup>3)</sup> | -       | 0.4                                | V    |

Note :

1. Industrial Product : T<sub>A</sub>=-40 to 85°C, otherwise specified
2. Overshoot : V<sub>CC</sub> + 1.0 V in case of pulse width ≤ 20ns
3. Undershoot : -1.0 V in case of pulse width ≤ 20ns
4. Overshoot and undershoot are sampled, not 100% tested.

CAPACITANCE<sup>1)</sup> (f=1MHz, T<sub>A</sub>=25°C)

| Item                     | Symbol          | Test Condition      | Min | Max | Unit |
|--------------------------|-----------------|---------------------|-----|-----|------|
| Input capacitance        | C <sub>IN</sub> | V <sub>IN</sub> =0V | -   | 8   | pF   |
| Input/Output capacitance | C <sub>IO</sub> | V <sub>IO</sub> =0V | -   | 10  | pF   |

1. Capacitance is sampled, not 100% tested

## DC AND OPERATING CHARACTERISTICS

| Item                           | Symbol           | Test Conditions                                                                                                                                 | Min | Typ | Max             | Unit |
|--------------------------------|------------------|-------------------------------------------------------------------------------------------------------------------------------------------------|-----|-----|-----------------|------|
| Input leakage current          | I <sub>LI</sub>  | V <sub>IN</sub> =V <sub>SS</sub> to V <sub>CC</sub>                                                                                             | -1  | -   | 1               | μA   |
| Output leakage current         | I <sub>LO</sub>  | $\overline{CS}=V_{IH}$ or $\overline{OE}=V_{IH}$ or $\overline{WE}=V_{IL}$ , V <sub>IO</sub> =V <sub>SS</sub> to V <sub>CC</sub>                | -1  | -   | 1               | μA   |
| Operating power supply current | I <sub>CC</sub>  | I <sub>IO</sub> =0mA, $\overline{CS}=V_{IL}$ , V <sub>IN</sub> =V <sub>IH</sub> or V <sub>IL</sub>                                              | -   | -   | 2               | mA   |
| Average operating current      | I <sub>CC1</sub> | Cycle time=1μs, 100%duty, I <sub>IO</sub> =0mA, $\overline{CS} \leq 0.2V$ , V <sub>IN</sub> ≤0.2V or V <sub>IN</sub> ≥V <sub>CC</sub> -0.2V     | -   | -   | 3               | mA   |
|                                | I <sub>CC2</sub> | Cycle time=Min, I <sub>IO</sub> =0mA, 100% duty, $\overline{CS}=V_{IL}$ , V <sub>IN</sub> =V <sub>IH</sub> or V <sub>IL</sub>                   | -   | -   | 25              | mA   |
| Output low voltage             | V <sub>OL</sub>  | I <sub>OL</sub> = 0.1mA                                                                                                                         | -   | -   | 0.2             | V    |
| Output high voltage            | V <sub>OH</sub>  | I <sub>OL</sub> = -0.1mA                                                                                                                        | 1.6 | -   | -               | V    |
| Standby Current(TTL)           | I <sub>SB</sub>  | $\overline{CS}=V_{IH}$ or $\overline{LB}=\overline{UB}=V_{IH}$ , Other inputs=V <sub>IH</sub> or V <sub>IL</sub>                                | -   | -   | 0.3             | mA   |
| Standby Current (CMOS)         | I <sub>SB1</sub> | $\overline{CS} \geq V_{CC}-0.2V$ or $\overline{LB}=\overline{UB} \geq V_{CC}-0.2V$ , $\overline{CS} \leq 0.2V$ , Other inputs=0~V <sub>CC</sub> | -   | 0.5 | 5 <sup>1)</sup> | μA   |

1. Super low power product=2μA with special handling.

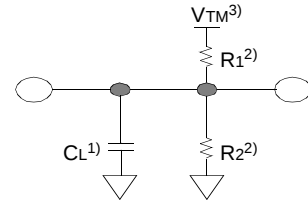
## AC OPERATING CONDITIONS

## TEST CONDITIONS (Test Load and Test Input/Output Reference)

Input pulse level : 0.2 to  $V_{CC}-0.2V$ 

Input rising and falling time : 5ns

Input and output reference voltage : 0.9V

Output load (See right) :  $C_L = 100pF + 1TTL$   
 $C_L = 30pF + 1TTL$ 

1. Including scope and jig capacitance

2.  $R_1 = 3070\Omega$ ,  $R_2 = 3150\Omega$ 3.  $V_{TM} = 1.8V$ AC CHARACTERISTICS ( $T_A = -40$  to  $85^\circ C$ ,  $V_{CC} = 1.7 \sim 2.2V$ )

| Parameter List |                                                            | Symbol | Speed Bins |     |       |     | Units |
|----------------|------------------------------------------------------------|--------|------------|-----|-------|-----|-------|
|                |                                                            |        | 85ns       |     | 100ns |     |       |
|                |                                                            |        | Min        | Max | Min   | Max |       |
| Read           | Read cycle time                                            | trc    | 85         | -   | 100   | -   | ns    |
|                | Address access time                                        | tAA    | -          | 85  | -     | 100 | ns    |
|                | Chip select to output                                      | tCO    | -          | 85  | -     | 100 | ns    |
|                | Output enable to valid output                              | tOE    | -          | 45  | -     | 50  | ns    |
|                | $\overline{UB}$ , $\overline{LB}$ Access Time              | tBA    | -          | 85  | -     | 100 | ns    |
|                | Chip select to low-Z output                                | tLZ    | 10         | -   | 10    | -   | ns    |
|                | $\overline{UB}$ , $\overline{LB}$ enable to low-Z output   | tBLZ   | 10         | -   | 10    | -   | ns    |
|                | Output enable to low-Z output                              | tOLZ   | 5          | -   | 5     | -   | ns    |
|                | Chip disable to high-Z output                              | tHZ    | 0          | 25  | 0     | 30  | ns    |
|                | $\overline{UB}$ , $\overline{LB}$ disable to high-Z output | tBHZ   | 0          | 25  | 0     | 30  | ns    |
|                | Output disable to high-Z output                            | tOHZ   | 0          | 25  | 0     | 30  | ns    |
|                | Output hold from address change                            | tOH    | 15         | -   | 15    | -   | ns    |
| Write          | Write cycle time                                           | tWC    | 85         | -   | 100   | -   | ns    |
|                | Chip select to end of write                                | tcw    | 70         | -   | 80    | -   | ns    |
|                | Address set-up time                                        | tAS    | 0          | -   | 0     | -   | ns    |
|                | Address valid to end of write                              | tAW    | 70         | -   | 80    | -   | ns    |
|                | $\overline{UB}$ , $\overline{LB}$ Valid to End of Write    | tBW    | 70         | -   | 80    | -   | ns    |
|                | Write pulse width                                          | tWP    | 60         | -   | 70    | -   | ns    |
|                | Write recovery time                                        | tWR    | 0          | -   | 0     | -   | ns    |
|                | Write to output high-Z                                     | tWHZ   | 0          | 25  | 0     | 30  | ns    |
|                | Data to write time overlap                                 | tdw    | 35         | -   | 40    | -   | ns    |
|                | Data hold from write time                                  | tdH    | 0          | -   | 0     | -   | ns    |
|                | End write to output low-Z                                  | tow    | 5          | -   | 5     | -   | ns    |

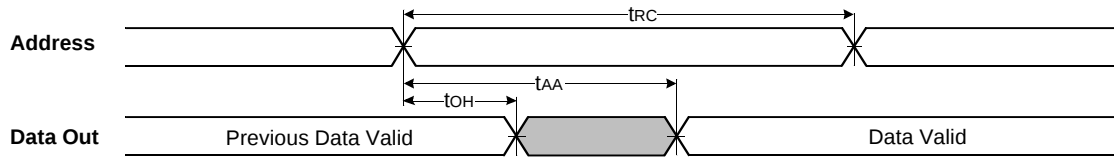
## DATA RETENTION CHARACTERISTICS

| Item                        | Symbol | Test Condition                                           | Min | Typ | Max       | Unit    |
|-----------------------------|--------|----------------------------------------------------------|-----|-----|-----------|---------|
| $V_{CC}$ for data retention | VDR    | $\overline{CS} \geq V_{CC}-0.2V^{(1)}$                   | 1.0 | -   | 2.2       | V       |
| Data retention current      | IDR    | $V_{CC} = 1.2V$ , $\overline{CS} \geq V_{CC}-0.2V^{(1)}$ | -   | 0.5 | $3^{(2)}$ | $\mu A$ |
| Data retention set-up time  | tSDR   | See data retention waveform                              | 0   | -   | -         | ns      |
| Recovery time               | trDR   |                                                          | trc | -   | -         |         |

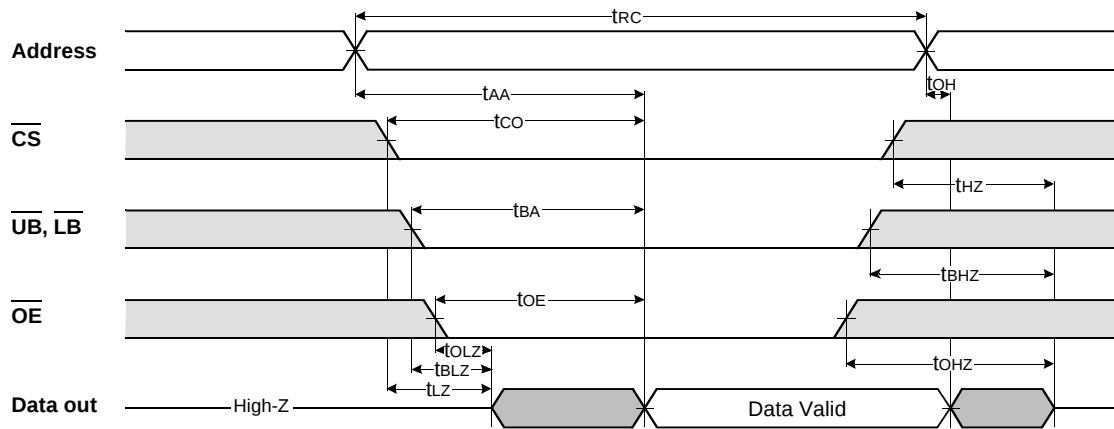
1.  $\overline{CS} \geq V_{CC}-0.2V$  ( $\overline{CS}$  controlled) or  $\overline{LB} = \overline{UB} \geq V_{CC}-0.2V$ ,  $\overline{CS} \leq 0.2V$  ( $\overline{LB}$ ,  $\overline{UB}$  controlled)2. Super low power product =  $2\mu A$  with special handling.

## TIMMING DIAGRAMS

**TIMING WAVEFORM OF READ CYCLE(1)** (Address Controlled,  $\overline{CS}=\overline{OE}=V_{IL}$ ,  $\overline{WE}=V_{IH}$ ,  $\overline{UB}$  or/and  $\overline{LB}=V_{IL}$ )



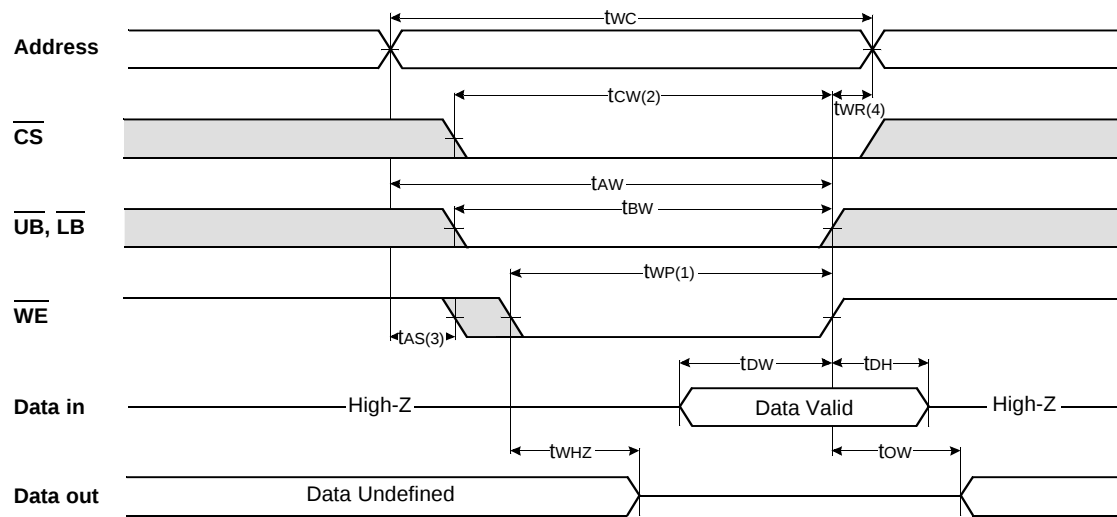
**TIMING WAVEFORM OF READ CYCLE(2)** ( $\overline{WE}=V_{IH}$ )



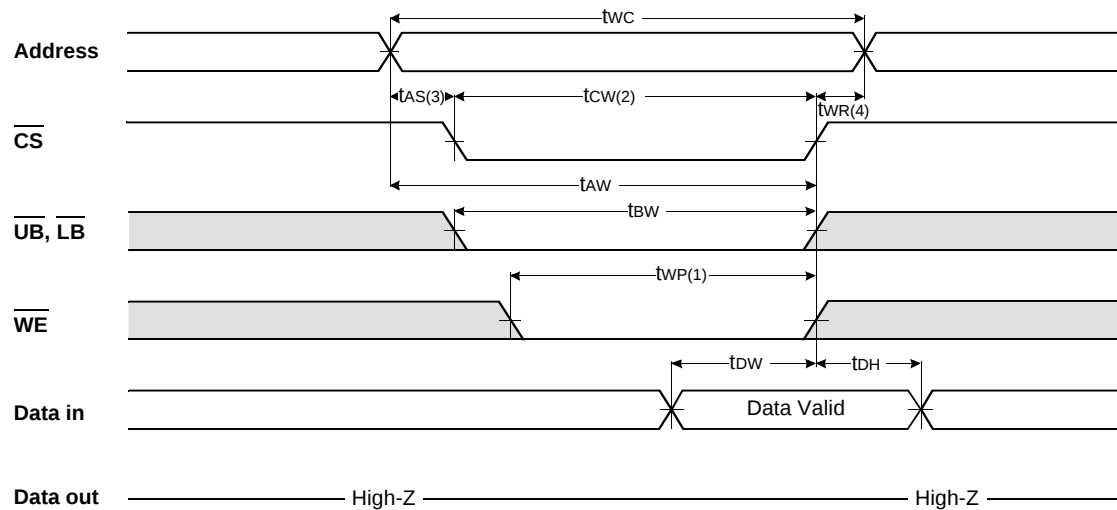
### NOTES (READ CYCLE)

1.  $t_{HZ}$  and  $t_{OHZ}$  are defined as the time at which the outputs achieve the open circuit conditions and are not referenced to output voltage levels.
2. At any given temperature and voltage condition,  $t_{HZ}(\text{Max.})$  is less than  $t_{LZ}(\text{Min.})$  both for a given device and from device to device interconnection.

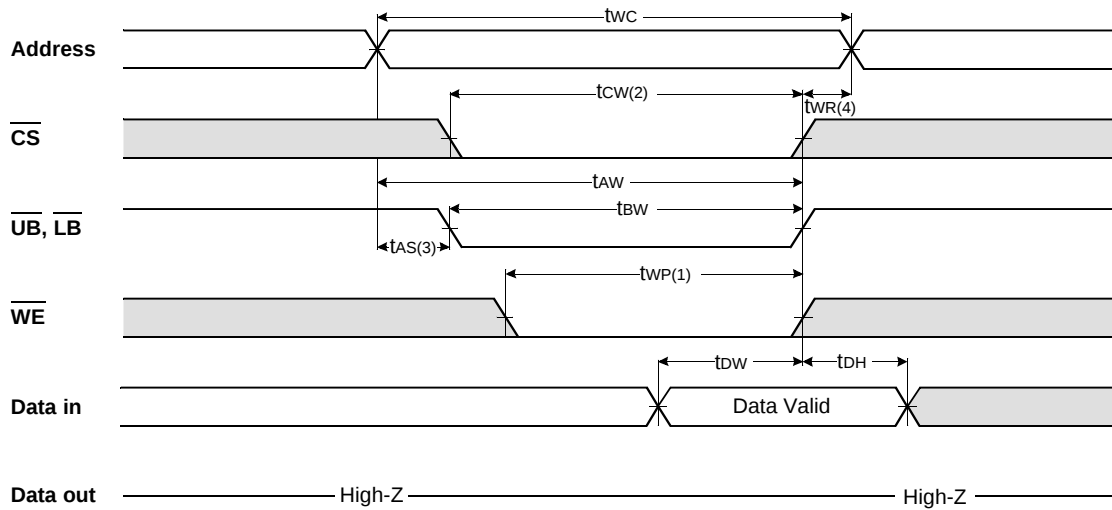
**TIMING WAVEFORM OF WRITE CYCLE(1) ( $\overline{WE}$  Controlled)**



**TIMING WAVEFORM OF WRITE CYCLE(2) ( $\overline{CS}$  Controlled)**



## TIMING WAVEFORM OF WRITE CYCLE(3) ( $\overline{UB}$ , $\overline{LB}$ Controlled)

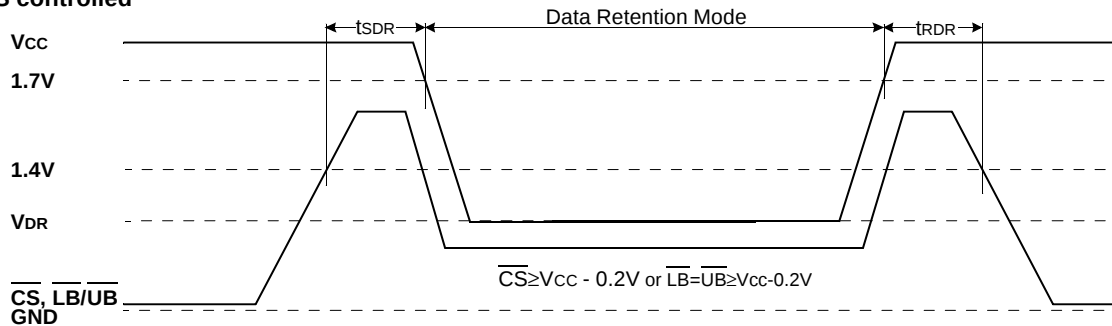


### NOTES (WRITE CYCLE)

1. A write occurs during the overlap( $t_{WP}$ ) of low  $\overline{CS}$  and low  $\overline{WE}$ . A write begins when  $\overline{CS}$  goes low and  $\overline{WE}$  goes low with asserting  $\overline{UB}$  or  $\overline{LB}$  for single byte operation or simultaneously asserting  $\overline{UB}$  and  $\overline{LB}$  for double byte operation. A write ends at the earliest transition when  $\overline{CS}$  goes high and  $\overline{WE}$  goes high. The  $t_{WP}$  is measured from the beginning of write to the end of write.
2.  $t_{CW}$  is measured from the  $\overline{CS}$  going low to end of write.
3.  $t_{AS}$  is measured from the address valid to the beginning of write.
4.  $t_{WR}$  is measured from the end of write to the address change.  $t_{WR}$  applied in case a write ends as  $\overline{CS}$  or  $\overline{WE}$  going high.

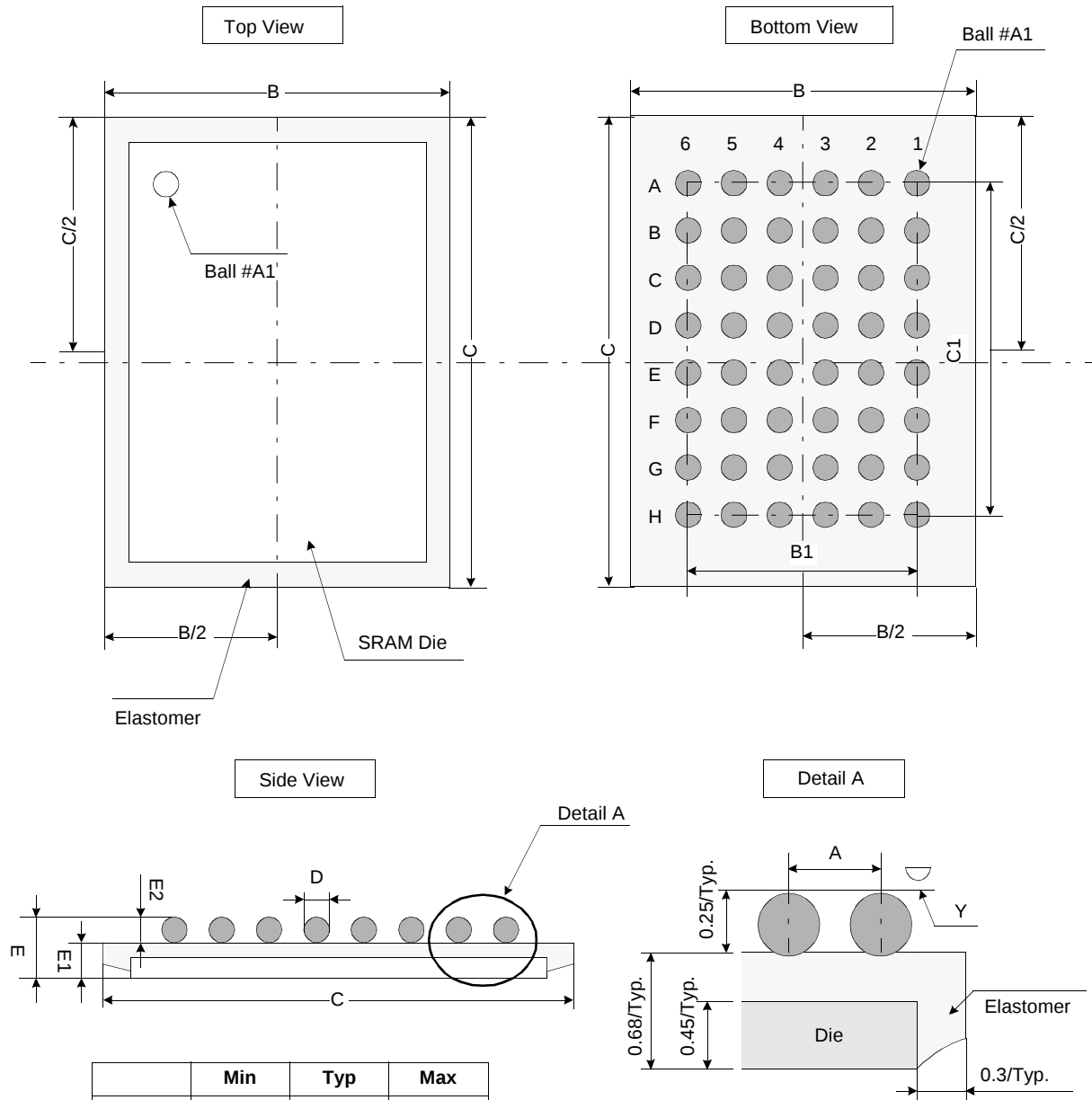
## DATA RETENTION WAVE FORM

### $\overline{CS}$ controlled



## PACKAGE DIMENSIONS

Unit : millimeter(inch)



### Notes.

1. Bump counts : 48(8row x 6column)
2. Bump pitch : (x,y)=(0.75 x 0.75)(typ.)
3. All tolerance are +/-0.050 unless otherwise specified.
4. Typ : Typical
5. Y is coplanarity : 0.08(Max)